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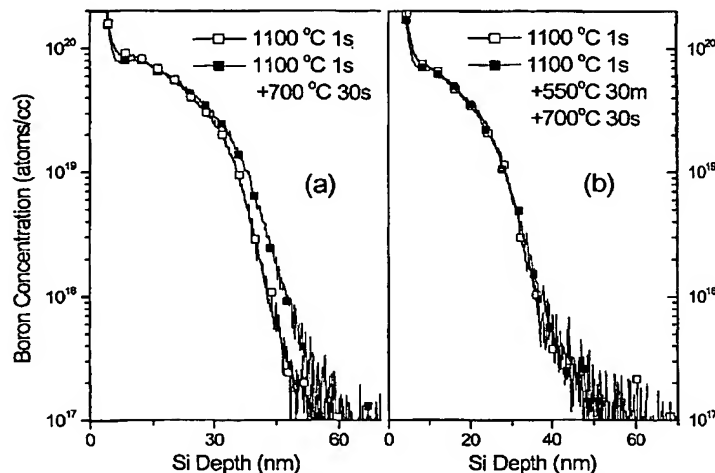
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- (71) Applicant (for all designated States except US): **UNIVERSITY OF HOUSTON** [US/US]; 4800 Calhoun Road, Houston, TX 77204-2015 (US).
- (72) Inventors; and
- (75) Inventors/Applicants (for US only): **CHU, Wei-Kan** [US/US]; 4800 Calhoun Road, Houston, TX 77204 (US). **SHAO, Lin** [CN/US]; 4800 Calhoun Road, Houston, TX 77204-2015 (US). **LIU, Jiarui** [US/US]; 4800 Calhoun Road, Houston, TX 77204-2015 (US).
- (74) Agents: **HEADLEY, Tim** et al.; Gardere Wynne Sewell LLP, 1000 Louisiana, Suite 3400, Houston, TX 77002-5007 (US).
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(54) Title: METHOD TO OVERCOME INSTABILITY OF ULTRA-SHALLOW SEMICONDUCTOR JUNCTIONS



(57) Abstract: A method of forming a stable junction on a microelectronic structure on a semiconductor wafer having a silicon surface layer on a substrate includes the following steps: implanting dopant ions into the surface layer; cleaning and oxidizing the surface layer, and twice annealing the wafer to recover a damaged silicon crystal structure of the surface layer resulting from the low energy ion implantation. The first annealing process uses a temperature range of 800°C to 1200°C for a duration from about a fraction of a second to less than about 1000 seconds, with a ramp-up rate of about 50°C/second to about 1000°C/second. The second annealing process uses a temperature range of 400°C to 650°C for a time period of from about 1 second to about 10 hours, and more preferably, from about 60 seconds to about 1 hour. Both annealing processes include cooling processes.